BD136G, BD138G, BD140G

Plastic Medium-Power Silicon PNP Transistors

This series of plastic, medium-power silicon PNP transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- BD 136, 138, 140 are complementary with BD 135, 137, 139
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD136G BD138G BD140G	V _{CEO}	45 60 80	Vdc
Collector-Base Voltage BD136G BD138G BD140G	V _{CBO}	45 60 100	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	Ic	1.5	Adc
Base Current	I _B	0.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.25 10	Watts mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	12.5 100	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

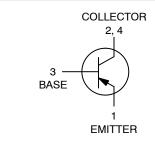
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	10	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	100	°C/W



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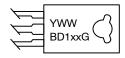
www.onsemi.com

1.5 A POWER TRANSISTORS PNP SILICON 45, 60, 80 V, 12.5 W





MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
BD136G	TO-225 (Pb-Free)	500 Units/Box
BD138G	TO-225 (Pb-Free)	500 Units/Box
BD140G	TO-225 (Pb-Free)	500 Units/Box

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BD136G, BD138G, BD140G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) (I _C = 0.03 Adc, I _B = 0) BD136G BD138G BD140G	BV _{CEO}	45 60 80	- - -	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_C = 125 ^{\circ}C)$	Ісво	- -	0.1 10	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	10	μAdc
DC Current Gain $ \begin{array}{l} \text{(I}_{C} = 0.005 \text{ A, V}_{CE} = 2 \text{ V)} \\ \text{(I}_{C} = 0.15 \text{ A, V}_{CE} = 2 \text{ V)} \\ \text{(I}_{C} = 0.5 \text{ A, V}_{CE} = 2 \text{ V)} \end{array} $	h _{FE} *	25 40 25	_ 250 _	-
Collector-Emitter Saturation Voltage (Note 1) (I _C = 0.5 Adc, I _B = 0.05 Adc)	V _{CE(sat)} *	-	0.5	Vdc
Base-Emitter On Voltage (Note 1) (I _C = 0.5 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)} *	-	1	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

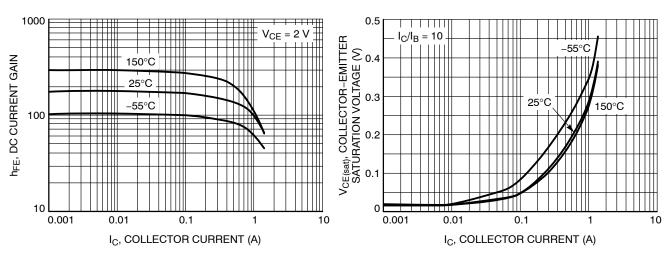


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BD136G, BD138G, BD140G

TYPICAL CHARACTERISTICS

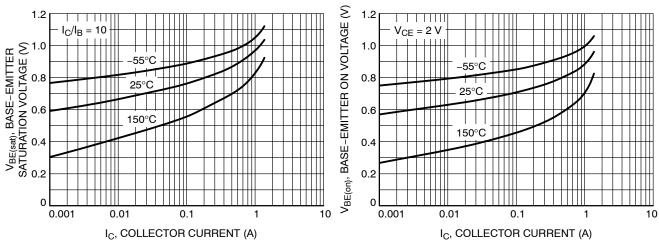


Figure 3. Base-Emitter Saturation Voltage

Figure 4. Base-Emitter On Voltage

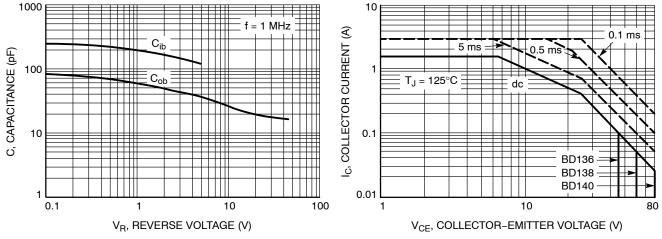


Figure 5. Capacitance

Figure 6. Active-Region Safe Operating Area

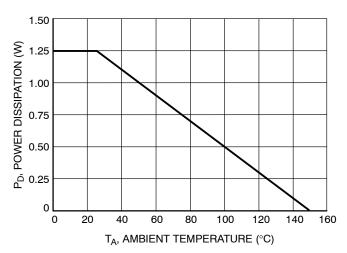
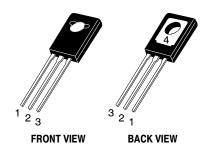


Figure 7. Power Derating

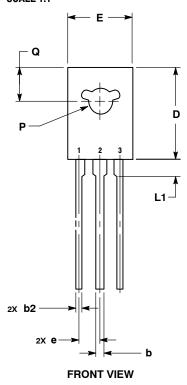
MECHANICAL CASE OUTLINE

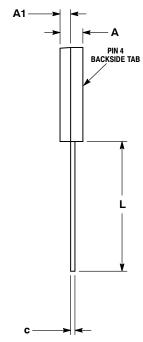


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1



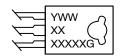


SIDE VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
С	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80 4.20				

GENERIC MARKING DIAGRAM*



= Year ww = Work Week XXXXX = Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

2., 4. DRAIN 3. GATE

= Pb-Free Package

	EMITTER COLLECTOR BASE	2., 4.	CATHODE ANODE GATE	STYLE 3: PIN 1. 2., 4. 3.	COLLECTOR	,	ANODE 1 ANODE 2 GATE	STYLE 5: PIN 1. 2., 4. 3.	
STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	MT 1	STYLE 8: PIN 1.	SOURCE	STYLE 9: PIN 1.	GATE	STYLE 10: PIN 1.	SOURCE

2., 4. GATE 3. DRAIN

DRAIN

2., 4. 3. DRAIN

2., 4. GATE 3. MT 2

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2., 4. 3. GATE

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